

Silicon PNP Power Transistors

2SB600

DESCRIPTION

- With TO-3 package
- High power dissipations
- Complement to type 2SD555

APPLICATIONS

- For use in audio and power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

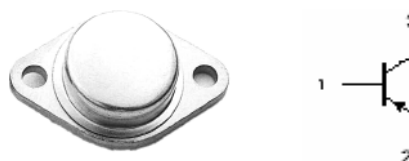


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-200	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-10	A
P_C	Collector power dissipation	$T_C = 25\square$	200	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~200	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-25mA ; I_B=0$	-200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1mA ; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-10A ; I_B=-1A$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-10A ; I_B=-1A$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-200V ; I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V ; I_C=0$			-0.1	mA
h_{FE}	DC current gain	$I_C=-2A ; V_{CE}=-5V$	20			
f_T	Transition frequency	$I_C=-0.5A ; V_{CE}=-10V$	4			MHz

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PACKAGE OUTLINE

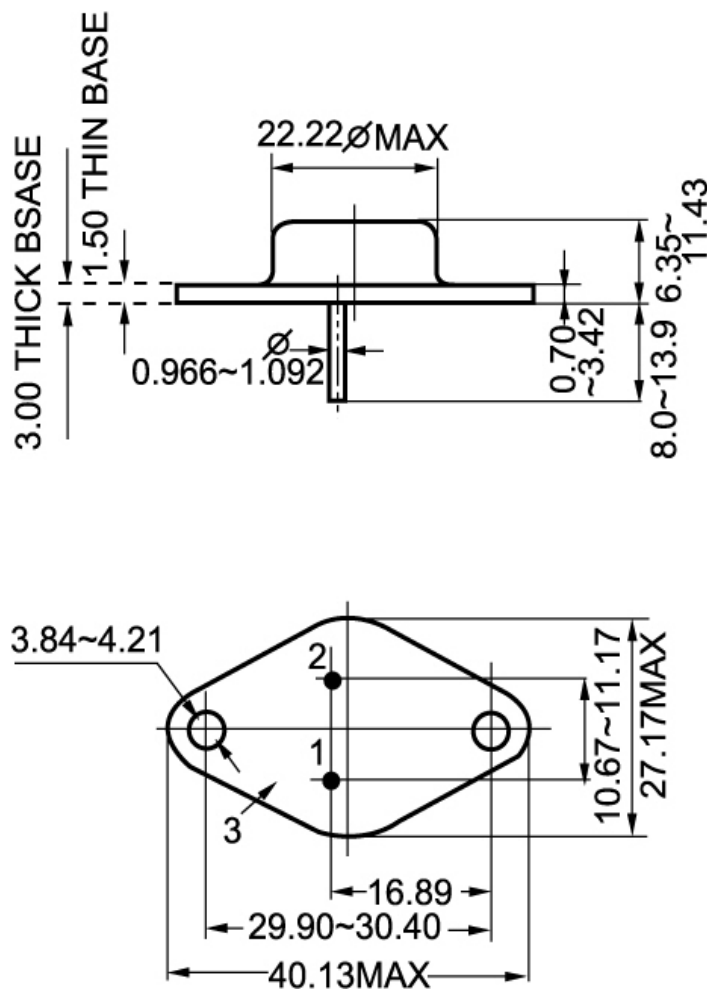


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)